

C1050-30

Near Infrared LED CHIP

<Specifications>

Commodity Type and Physical Characteristics	
Material	InGaAsP/InP
Top Side P(anode)side	Au Alloy
Bottom Side N(cathode)side	Au Alloy
Electrode Pattern	Fig.1
Chip Size	Fig.2
Chip Thickness	Fig.2
Emission Area	Fig.2

Electro-Optical Characteristics [Ta=25℃]						
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	IF=20mA		1.1	1.4	V
Reverse Current	IR	VR=3V			10	uA
Power Intensity*	PO	IF=20mA		0.6		mW
Peak Wavelength	λ P	IF=20mA		1050		nm
Spectral Radiation Bandwidth	$\Delta\lambda$	IF=20mA		60		nm
Rise Time	tr	IF=20mA		20		ns
Fall Time	tf	IF=20mA		20		ns

Die shall be mounted on TO-18 gold header without resin coated.

* Measured by PD G8370-85

[Unit:um]

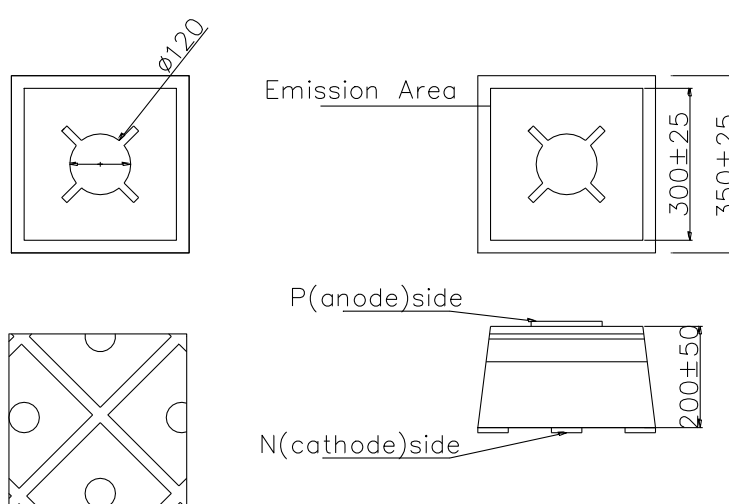


Fig.1 Electrode Pattern

Fig.2 Chip Size and Emission Area